



Standard Rectifier

$V_{RRM} = 2 \times 800 \text{ V}$
 $I_{FAV} = 8 \text{ A}$
 $V_F = 1.08 \text{ V}$

Phase leg

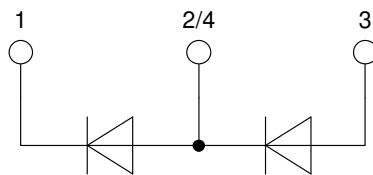
Part number

DSP8-08S

Marking on Product: DSP8-08S



Backside: anode/cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					900	V
V_{RRM}	max. repetitive reverse blocking voltage					800	V
I_R	reverse current	$V_R = 800\text{ V}$	$T_{VJ} = 25^\circ\text{C}$			10	μA
		$V_R = 800\text{ V}$	$T_{VJ} = 150^\circ\text{C}$			0.2	mA
V_F	forward voltage drop	$I_F = 8\text{ A}$	$T_{VJ} = 25^\circ\text{C}$			1.16	V
		$I_F = 16\text{ A}$				1.35	V
		$I_F = 8\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.08	V
		$I_F = 16\text{ A}$				1.34	V
I_{FAV}	average forward current	$T_C = 160^\circ\text{C}$ rectangular	$T_{VJ} = 175^\circ\text{C}$ d = 0.5			8	A
V_{FO}	threshold voltage	} for power loss calculation only				0.79	V
r_F	slope resistance					33	m Ω
R_{thJC}	thermal resistance junction to case					1.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.25		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		100	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			120	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			130	A
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			100	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			110	A
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			72	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			70	A ² s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			50	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			50	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		4	pF



Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			25	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				1.5		g
F_C	mounting force with clip		20		60	N

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSP8-08S-TRL	DSP8-08S	Tape & Reel	800	495670
Alternative	DSP8-08S-TUB	DSP8-08S	Tube	50	498793

Similar Part	Package	Voltage class
DSP8-08AS	TO-263AA (D2Pak) (3)	800
DSP8-08A	TO-220AB (3)	800
DSP8-12S	TO-263AB (D2Pak) (2)	1200
DSP8-12AS	TO-263AA (D2Pak) (3)	1200

DSP8-12A	TO-220AB (3)	1200
DSP8-12AC	ISOPLUS220AB (3)	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



Rectifier

$V_{0\ max}$	threshold voltage	0.79	V
$R_{0\ max}$	slope resistance *	30	mΩ



Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2.54 BSC		0.100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



Rectifier


Fig. 1 Forward current versus voltage drop per diode

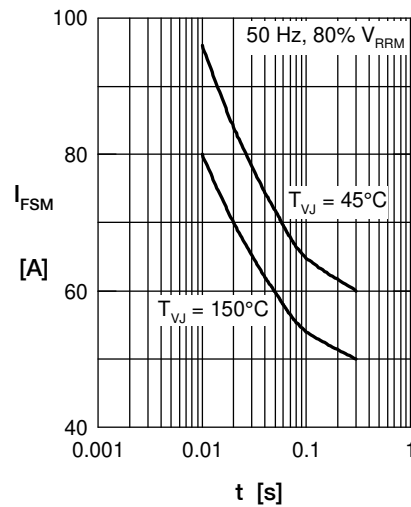


Fig. 2 Surge overload current

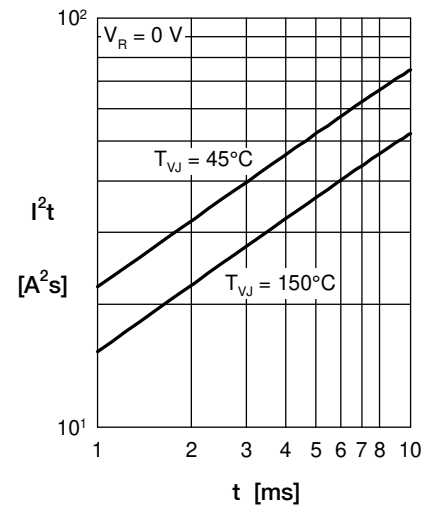
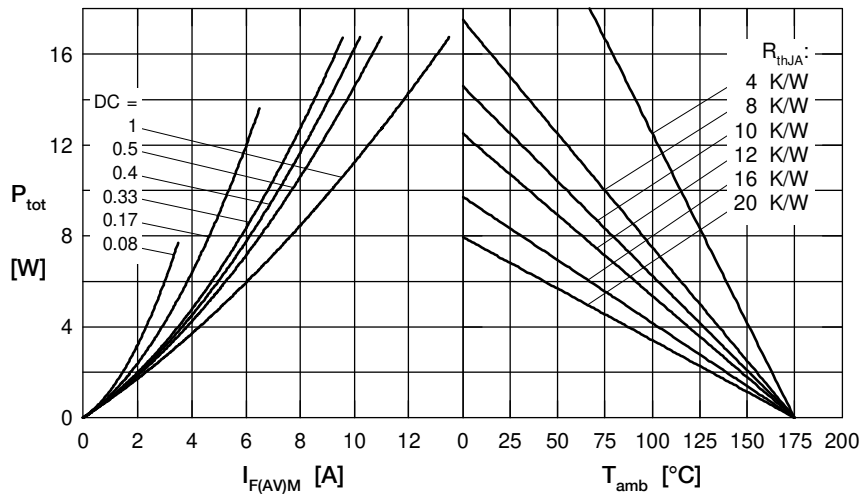

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. direct output current and ambient temperature

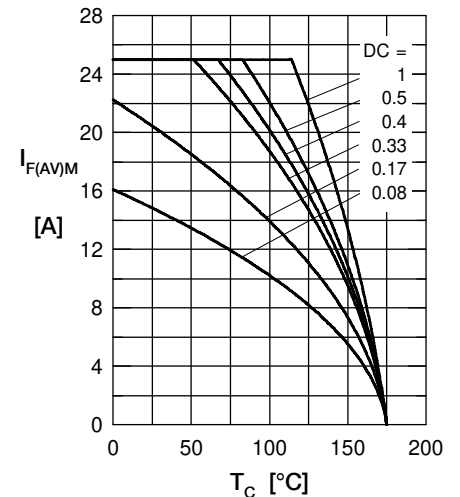


Fig. 5 Max. forward current vs. case temperature

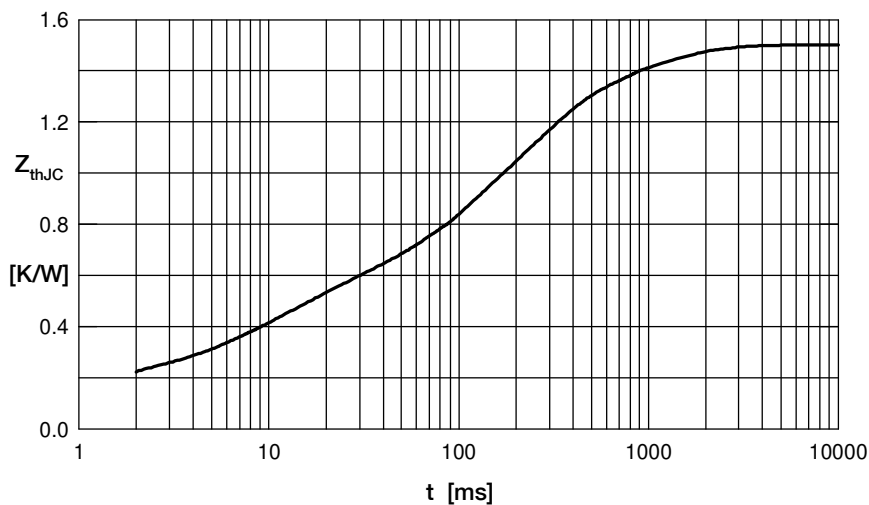


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.155	0.0005
2	0.332	0.0095
3	0.713	0.17
4	0.3	0.8
5	0.00001	0.00001